



Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

I_{GT}	$V_D=12V R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=150$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	40	mA
				50	
I_H	$I_T=100mA$		MAX.	30	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150$		MIN.	1200	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s, T_j=150$		MIN.	8	A/ms
t_{on}	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	3	μs
t_{off}				30	

STATIC CHARACTERISTICS

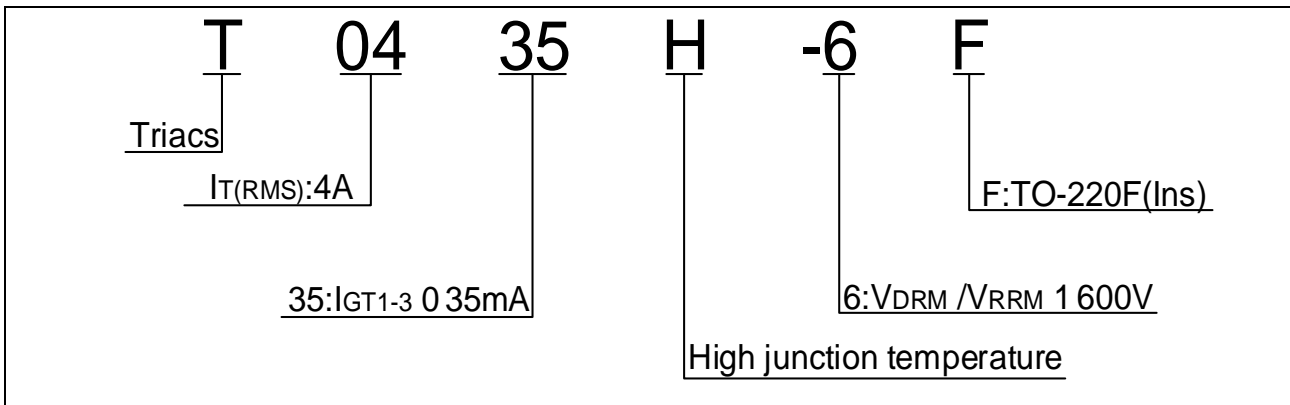
V_{TM}	$I_{TM}=5.5A t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=150$	0.6	V
R_D	Dynamic resistance	$T_j=150$	129	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	0.8	mA

THERMAL RESISTANCES

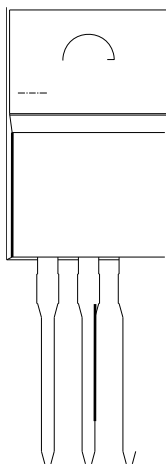
$R_{th(j-c)}$	junction to case (AC)	4	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W



ORDERING INFORMATION

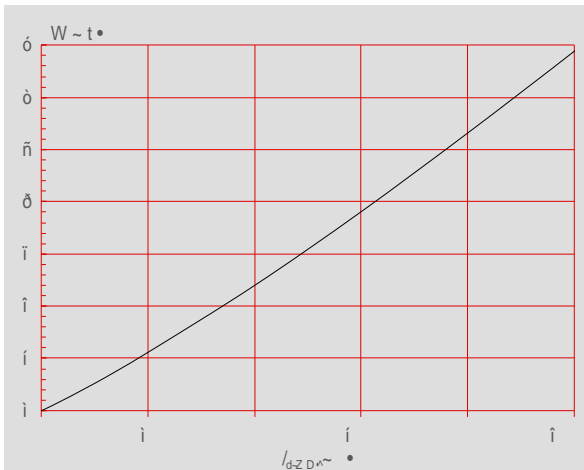


MARKING

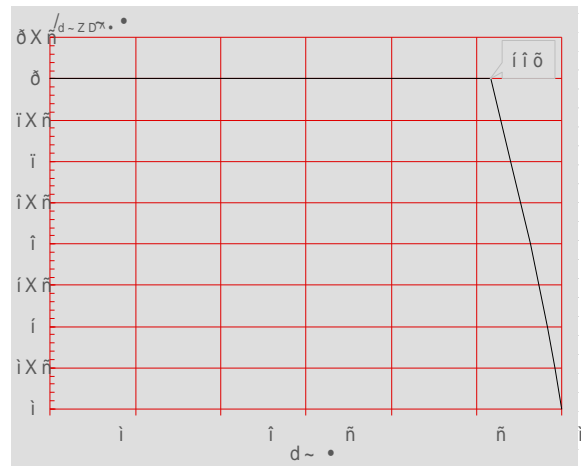




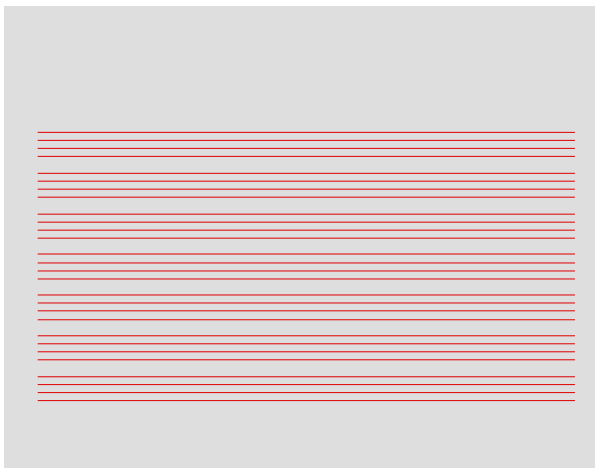
Maximum power dissipation versus RMS on-state current



RMS on-state current versus case temperature



Surge peak on-state current versus number of cycles



On-state characteristics



ORDERING INFORMATION

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated
Oct.10, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA



PACKAGE MECHANICAL DATA





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